

## ABSTRACT

In a vapor phase growth apparatus for performing a vapor phase growth of a silicon epitaxial layer on a main surface of a silicon single crystal substrate while heating the silicon single crystal substrate placed on a pocket formed on a susceptor, from both sides, the pocket has an outer peripheral side part which supports a rear surface of the silicon single crystal substrate and an inner peripheral side part which is kept in a state of being more recessed than the outer peripheral side part in the inside of the outer peripheral side part, and the susceptor has a warped inverted U-shaped longitudinal sectional shape.